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Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 28953.2004	Application No. 10/594,846 <del>New - unassigned</del>
<b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Makoto Iwai et al	<b>10/594846</b> Group Art Unit 1792
		Filing Date 11/08/2006 <del>Herewith</del>	

### U.S. Patent Documents

Examiner Initial	Desig. ID	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
/F.H./	AA	6,949,140	9/2005	Sarayama et al	117	81	
/F.H./	AB	6,398,867	6/2002	D'Evelyn et al	117	11	

### Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publn. Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
/F.H./	AC	2002-293696	10/2002	Japan			Abstract	
/F.H./	AD	2003-292400	10/2003	Japan			Abstract	
/F.H./	AE	2003-511326	3/2003	Japan			X	
/F.H./	AF	2005-8444	1/2005	Japan			Abstract	
/F.H./	AG	WO2004/013385	6/2003	WIPO			Abstract	
/F.H./	AH	WO01/024921	9/2000	WIPO				
	AI							
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	AL							
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	AN							
	AO							

### Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
/F.H./	AP	Kawamura, F. et al, "Growth of a Large GaN Single Crystal Using the Liquid Phase Epitaxy (LPE) Technique," Jpn. J. Appl. Phys., Vol. 42 (2003), pp. L4-L6
	AQ	
	AR	
	AS	
	AT	

Examiner Signature /Felisa Hiteshew/	Date Considered 04/11/2008
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Disclosure Form (PTO-1449)

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /F.H./